1000 Ω GaAs thin-film resistor die

LCRES-R1000OHM — 1000 Ω GaAs thin-film resistor die.

Resistance: 1000 Ω (typical); Linear operating current: 0.04 A (typical); Maximum allowable current: 0.08 A (maximum). Plan-view die dimensions: 0.5 × 0.5 mm.



Electrical characteristics

TA = +25 °C

Parameter	Symbol	Minimum	Typical	Maximum	Value	Unit
Resistor count	-	-	-	-	1	-
Terminal count	-	-	-	-	2	-
Resistance	-	-	1000	-	-	Ω
Resistance tolerance	-	-	±5	-	-	%
Linear operating current	-	-	0.04	-	-	A

Absolute limits

Parameter	Symbol	Minimum	Typical	Maximum	Unit
Maximum allowable current	-	-	-	0.08	A

Environmental specifications

Parameter	Symbol	Minimum	Typical	Maximum	Unit
Storage temperature	-	-65	-	150	°C
Operating temperature	-	-55	-	125	°C

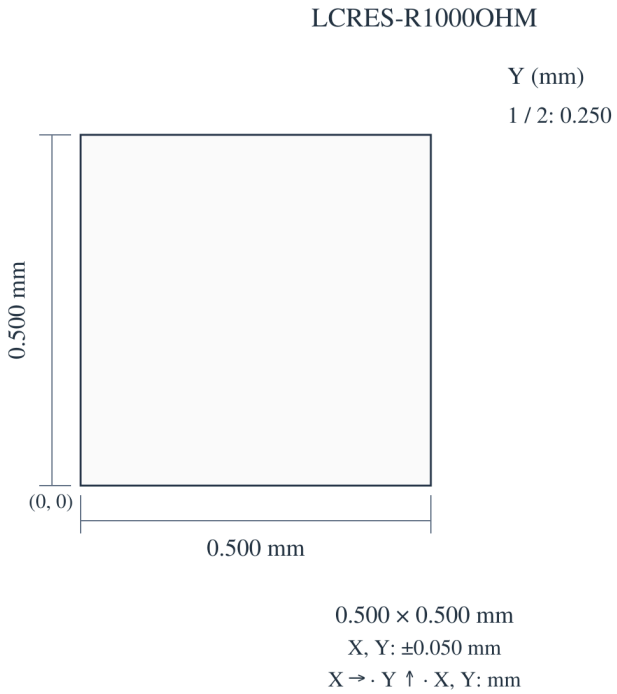
Bond-pad assignments

Pins	Symbol	Function	Notes
1, 2	IN/OUT	Reciprocal input/output	-
Die backside	GND	Ground	RF / DC GND

Die dimensions

Parameter	Value	Unit
Plan-view die dimensions	0.5 × 0.5	mm

Reference drawing showing selected dimensions in mm. Use complete drawings for fabrication and wire bonding.



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Die integration and bias sequencing

The die backside requires a reliable ground connection.

Document notice

Specifications are subject to revision. Before design release, confirm the current document revision and product-specific requirements with LCRF. The approved quotation and order documentation define the supplied configuration.